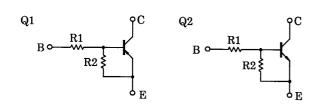
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

# **RN4905**

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

#### **Equivalent Circuit and Bias Resister Values**



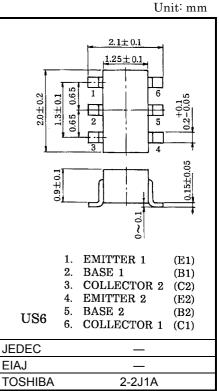
R2:  $47k\Omega$  (Q1, Q2 Common)

R1: 2.2kΩ

1

### Q1 Maximum Ratings (Ta = 25°C)

| Characteristic            | Symbol           | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage    | $V_{CBO}$        | -50    | V    |
| Collector-emitter voltage | $V_{CEO}$        | -50    | V    |
| Emitter-base voltage      | V <sub>EBO</sub> | -5     | V    |
| Collector current         | IC               | -100   | mA   |



Weight: 6.8mg

#### Q2 Maximum Ratings (Ta = 25°C)

| Characteristic            | Symbol           | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage    | V <sub>CBO</sub> | 50     | V    |
| Collector-emitter voltage | V <sub>CEO</sub> | 50     | V    |
| Emitter-base voltage      | V <sub>EBO</sub> | 5      | V    |
| Collector current         | Ic               | 100    | mA   |

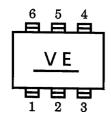
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### Q1, Q2 Common Maximum Ratings (Ta = 25°C)

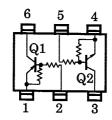
| Characteristic              | Symbol           | Rating  | Unit |
|-----------------------------|------------------|---------|------|
| Collector power dissipation | P <sub>C</sub> * | 200     | mW   |
| Junction temperature        | Tj               | 150     | °C   |
| Storage temperature range   | T <sub>stg</sub> | -55~150 | °C   |

<sup>\* :</sup> Total rating

### Marking



## **Equivalent Circuit (Top View)**



## Q1 Electrical Characteristics (Ta = 25°C)

| Characteristic                       | Symbol                | Test<br>Circuit | Test Condition                                  | Min    | Тур. | Max    | Unit |
|--------------------------------------|-----------------------|-----------------|---|--------|------|--------|------|
| Collector cut-off current            | I <sub>CBO</sub>      | _               | $V_{CB} = -50V, I_{E} = 0$                      | _      | _    | -100   | nA   |
|                                      | I <sub>CEO</sub>      | _               | $V_{CE} = -50V, I_B = 0$                        | _      | _    | -500   | ПА   |
| Emitter cut-off current              | I <sub>EBO</sub>      | _               | V <sub>EB</sub> = -5V, I <sub>C</sub> = 0       | -0.078 | _    | -0.145 | mA   |
| DC current gain                      | h <sub>FE</sub>       | _               | V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA   | 80     | _    | _      | _    |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub> | _               | I <sub>C</sub> = -5mA, I <sub>B</sub> = -0.25mA | _      | -0.1 | -0.3   | V    |
| Input voltage (ON)                   | V <sub>I (ON)</sub>   | _               | $V_{CE} = -0.2V, I_{C} = -5mA$                  | -0.6   | _    | -1.1   | V    |
| Input voltage (OFF)                  | V <sub>I (OFF)</sub>  | _               | V <sub>CE</sub> = -5V, I <sub>C</sub> = -0.1mA  | -0.5   | _    | -0.8   | V    |
| Transition frequency                 | f <sub>T</sub>        | _               | $V_{CE} = -10V, I_{C} = -5mA$                   | _      | 200  | _      | MHz  |
| Collector output capacitance         | C <sub>ob</sub>       | _               | V <sub>CB</sub> = −10V, I <sub>E</sub> = 0      | _      | 3    | 6      | pF   |

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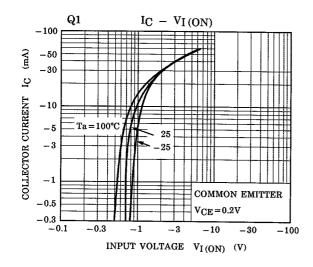
### Q2 Electrical Characteristics (Ta = 25°C)

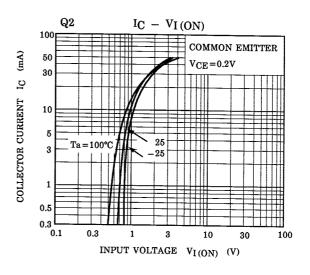
| Characteristic                       | Symbol                | Test<br>Circuit | Test Condition                                       | Min   | Тур. | Max   | Unit |
|--------------------------------------|-----------------------|-----------------|--|-------|------|-------|------|
| Collector cut-off current            | I <sub>CBO</sub>      | _               | V <sub>CB</sub> = 50V, I <sub>E</sub> = 0            | _     | _    | 100   | nA   |
|                                      | I <sub>CEO</sub>      | _               | V <sub>CE</sub> = 50V, I <sub>B</sub> = 0            | _     | -    | 500   |      |
| Emitter cut-off current              | I <sub>EBO</sub>      | _               | $V_{EB} = 5V, I_C = 0$                               | 0.078 | _    | 0.145 | mA   |
| DC current gain                      | h <sub>FE</sub>       | _               | V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA          | 80    | _    | _     | _    |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub> | _               | I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA        | _     | 0.1  | 0.3   | V    |
| Input voltage (ON)                   | V <sub>I (ON)</sub>   | _               | V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA         | 0.6   | _    | 1.1   | V    |
| Input voltage (OFF)                  | V <sub>I (OFF)</sub>  | _               | V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA         | 0.5   | _    | 0.8   | V    |
| Transition frequency                 | f <sub>T</sub>        | _               | V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA          | _     | 250  | _     | MHz  |
| Collector output capacitance         | C <sub>ob</sub>       | _               | V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1 MHz | _     | 3    | 6     | pF   |

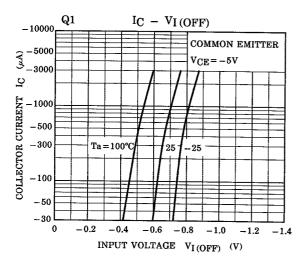
## Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

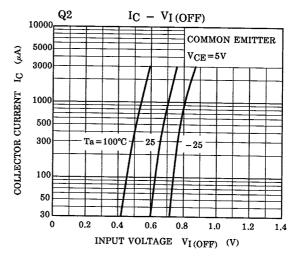
| Characteristic | Symbol | Test<br>Circuit | Test Condition | Min    | Тур.   | Max    | Unit |
|----------------|--------|-----------------|----------------|--------|--------|--------|------|
| Input resistor | R1     | _               | _              | 1.54   | 2.2    | 2.86   | kΩ   |
| Resistor ratio | R1/R2  | _               |                | 0.0421 | 0.0468 | 0.0515 | _    |

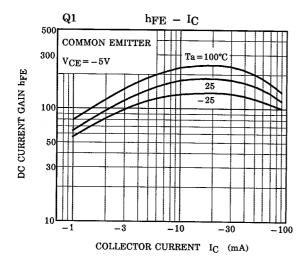
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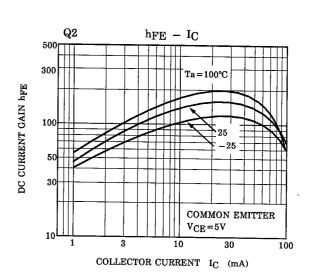












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